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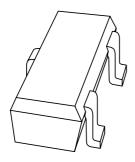
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



2PB709AWPNP general purpose transistor

Product data sheet 2002 Jun 26



PNP general purpose transistor

2PB709AW

FEATURES

- High collector current (max. 100 mA)
- Low collector-emitter saturation voltage (max. 500 mV).

APPLICATIONS

· General purpose switching and amplification.

DESCRIPTION

PNP transistor in an SC-70 (SOT323) plastic package. NPN complement: 2PD601AW

MARKING

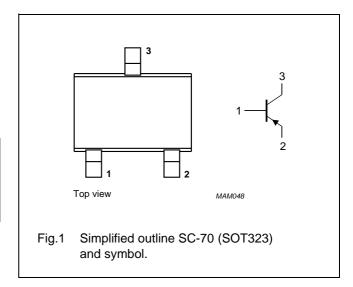
TYPE NUMBER	MARKING CODE ⁽¹⁾
2PB709AQW	N5*
2PB709ARW	N7*
2PB709ASW	N9*

Note

- 1. * = p: made in Hong Kong.
 - * = t: made in Malaysia.

PINNING

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-45	٧
V _{CEO}	collector-emitter voltage	open base	-	-45	٧
V _{EBO}	emitter-base voltage	open collector	_	-6	٧
I _C	collector current (DC)		-	-100	mA
I _{CM}	peak collector current		-	-200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	200	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. For mounting conditions, see "Thermal considerations and footprint design for SOT323 in the General Part of Data Handbook SC18".

2002 Jun 26 2

PNP general purpose transistor

2PB709AW

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. For mounting conditions, see "Thermal considerations and footprint design for SOT323 in the General Part of Data Handbook SC18".

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	I _E = 0; V _{CB} = -45 V	_	-10	nA
		$I_E = 0$; $V_{CB} = -45 \text{ V}$; $T_j = 150 ^{\circ}\text{C}$	_	-5	μΑ
I _{EBO}	emitter-base cut-off current	$I_C = 0; V_{EB} = -5 \text{ V}$	_	-10	nA
h _{FE}	DC current gain	$I_C = -2 \text{ mA}; V_{CE} = -10 \text{ V}$			
	2PB709AQW		160	260	
	2PB709ARW		210	340	
	2PB709ASW		290	460	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -100 \text{ mA}$; $I_B = -10 \text{ mA}$; note 1	_	-500	mV
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = -10 \text{ V}$; $f = 1 \text{ MHz}$	_	5	pF
f _T	transition frequency	$I_C = -1 \text{ mA}; V_{CE} = -10 \text{ V};$			
	2PB709AQW	f = 100 MHz	60	_	MHz
	2PB709ARW		70	_	MHz
	2PB709ASW		80	_	MHz

Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

2002 Jun 26 3

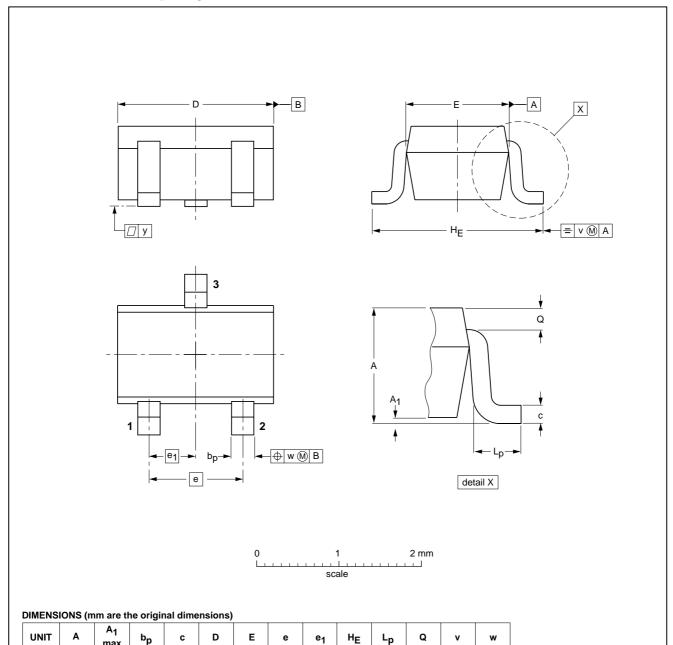
PNP general purpose transistor

2PB709AW

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



OUTLINE	REFERENCES		EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	1330E DATE
SOT323			SC-70			97-02-28

0.65

0.23 0.13

0.2

0.45

0.15

2002 Jun 26 4

0.4 0.3

1.1

mm

0.1

0.25

0.10

2.2

1.8

1.35

1.15

1.3

PNP general purpose transistor

2PB709AW

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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2002 Jun 26 5

NXP Semiconductors

Customer notification

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Contact information

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